

VERSION WITH MARKINGS TO SHOW CHANGES MADE

IN THE SPECIFICATION

Please replace the paragraph at page 5, line 30 to page 6, line 2, with the following:

Reference numerals 106', 110, and 114 denote a second dielectric layer, an inter-metal dielectric layer (IMD), and a passivation layer, respectively. These layers are dielectric layers used to sequentially form the second metal layer 112, the first metal layer 108, and the polysilicon film plate 104.

IN THE CLAIMS

1. (Once amended) A bonding pad of a semiconductor device, said bonding pad comprising:

- a substructure formed on a semiconductor substrate;
- a first dielectric layer formed on the substructure;
- a polysilicon film plate formed on the first dielectric layer [and configured to improve the resistance of the bonding pad to stress induced during wire bonding];
- a second dielectric layer formed overlying the polysilicon film plate, the second dielectric layer having a first opening that expose a region of the polysilicon film plate,
- a first metal layer formed on the polysilicon film plate through the first opening;
- an inter-metal dielectric (IMD) layer formed overlying the first metal layer, the inter-metal dielectric layer having a second opening that exposes a region of the first metal layer;
- [and]
- a second metal layer formed on the first metal layer in the second opening; and
- a passivation layer formed overlying the second metal layer, the passivation layer having a third opening that exposes a region of the second metal layer as a bonding pad.

20. (Once amended) A bonding pad of a semiconductor device, said bonding pad comprising:

- a substructure formed on a semiconductor substrate;
- a first dielectric layer formed on the substructure;
- a polysilicon film plate formed on the first dielectric layer and configured to improve the resistance of the bonding pad to stress created during wire bonding;
- a first metal layer formed on the polysilicon film plate, wherein the first metal layer is formed having a recessed area; [and]

a second metal layer formed on the first metal layer, wherein a portion of the second metal layer is arranged within the recessed area of the first metal layer to improve the resistance of the bonding pad to stress; and

a passivation layer formed overlying the second metal layer having an opening that exposes the second metal layer as a bonding pad.

Claim 21 is new.